Memory Testing

Memory ICs are a core component of nearly every electronic device. Memory ICs are usually categorized in volatile and non-volatile memory where volatile memory keeps its stored information when the power cycle is interrupted and volatile memory needs a constant power supply to retain its data. Most memory modules have a standardized format which can be tested with standardized test-pins. C.C.P. offers testing solutions for all common formats (DDR, Flash, eMCP, etc.) as well as customized testing solutions for your individual needs.

Design Concept

DDR2/3 Socket

DDR3/4 Socket

eMCP Socket

Housing	Material
Injection molding	PES

Housing	SPEC
Min. Pitch	0.4mm

Manual DDR2/3 Testing Module
Single Side

Manual DDR3 Testing Module
Double Side

ManualDDR2/3 Testing Module	SPEC
Max. Site Amount	8~16 (Single side/ Double side)
Transmission Rate (MT/s)	200MHz~1866MHz

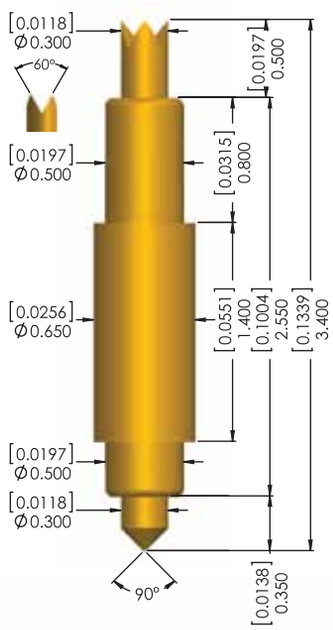
*All specifications are subject to changes without prior notification

Probe Specification

Unit:mm; [ ]:in

DE2-050EF25-120

DDR 2/3



Material

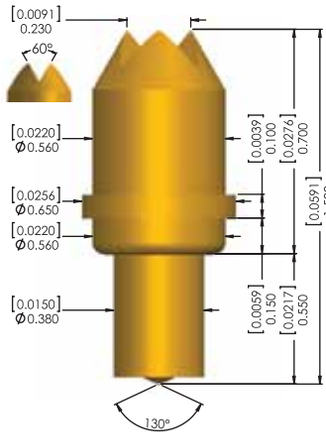
Top Plunger
BeCu, Au plated
Barrel
Brass , Au plated
Spring
SUS , Au plated
Bottom plunger
BeCu, Au plated

Mechanical Spec.

Recommended travel
0.40mm
Full travel
0.60mm
Spring force
35g±20%@0.40mm
Operating Temp.
-55°C~150°C

DE4-056EF09-03F0

DDR3

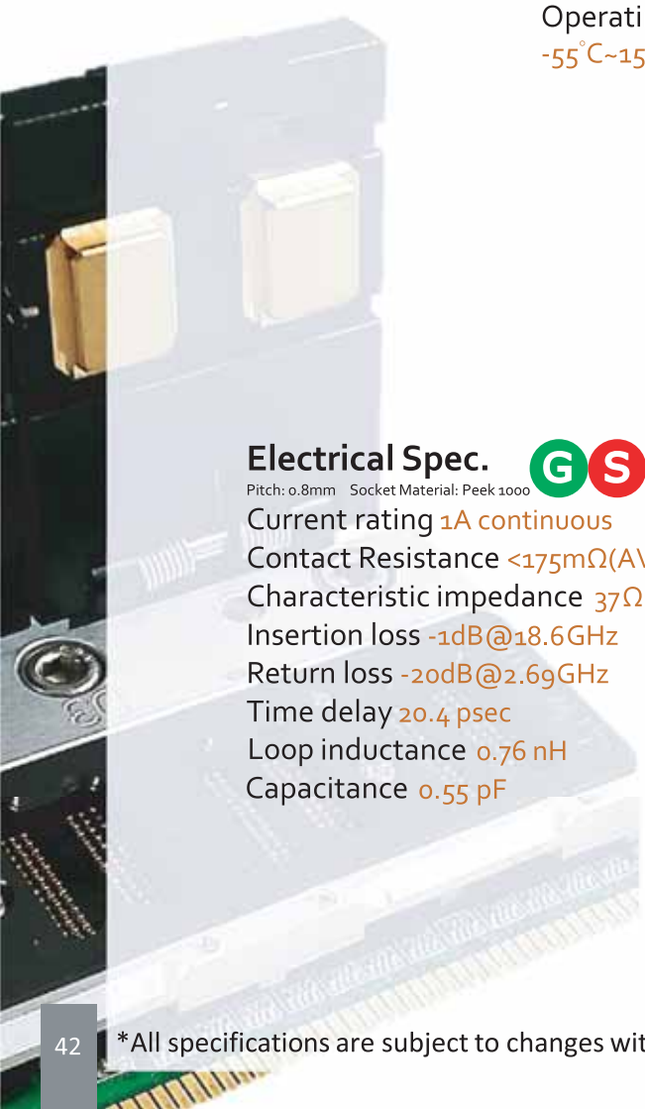


Material

Barrel
BeCu, Au plated
Spring
SUS , Au plated
Bottom plunger
BeCu, Au plated

Mechanical Spec.

Recommended travel
0.40mm
Full travel
0.50mm
Spring force
30g±20%@0.40mm
Operating Temp.
-55°C~150°C



Electrical Spec.

GSG

Pitch: 0.8mm Socket Material: Peek 1000

Current rating 1A continuous
Contact Resistance <175mΩ(AVG)
Characteristic impedance 37Ω
Insertion loss -1dB@18.6GHz
Return loss -20dB@2.69GHz
Time delay 20.4 psec
Loop inductance 0.76 nH
Capacitance 0.55 pF

Electrical Spec.

GSG

Pitch: 0.8mm Socket Material: Peek 1000

Current rating 1A continuous
Contact Resistance <75mΩ(AVG)
Characteristic impedance 36.16Ω
Insertion loss -1dB>20GHz
Return loss -20dB@5.11GHz
Time delay 9.4psec
Loop inductance 0.34nH
Capacitance 0.26pF

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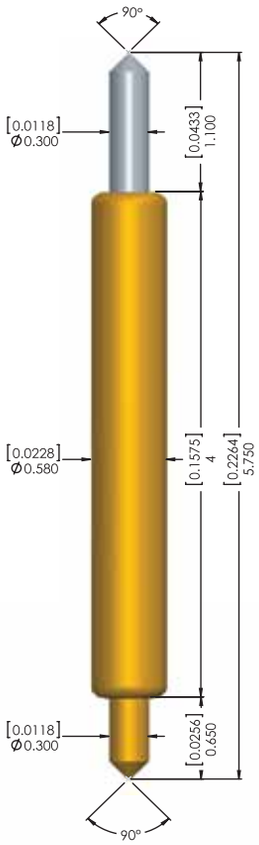
Probe Specification

Unit:mm; [ ]:in

PE1-058EE40-01A0 Flash



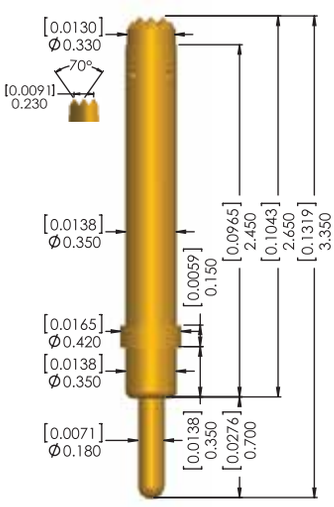
Material

Top Plunger
Pd alloy
Barrel
PhBz , Au plated
Spring
SUS, Au plated
Bottom plunger
BeCu , Au plated

Mechanical Spec.

Recommended travel
0.80mm
Full travel
1.1mm
Spring force
28g±20%@0.80mm
Operating Temp.
-55°C~150°C

DE4-035DH24-01A0 eMCP



Material

Top Plunger
BeCu , Au plated
Barrel
PhBz , Au plated
Spring
SWP , Au plated
Bottom plunger
BeCu , Au plated

Mechanical Spec.

Recommended travel
0.50mm
Full travel
0.70mm
Spring force
27g±20%@0.50mm
Operating Temp.
-15°C~125°C

Electrical Spec. G S G

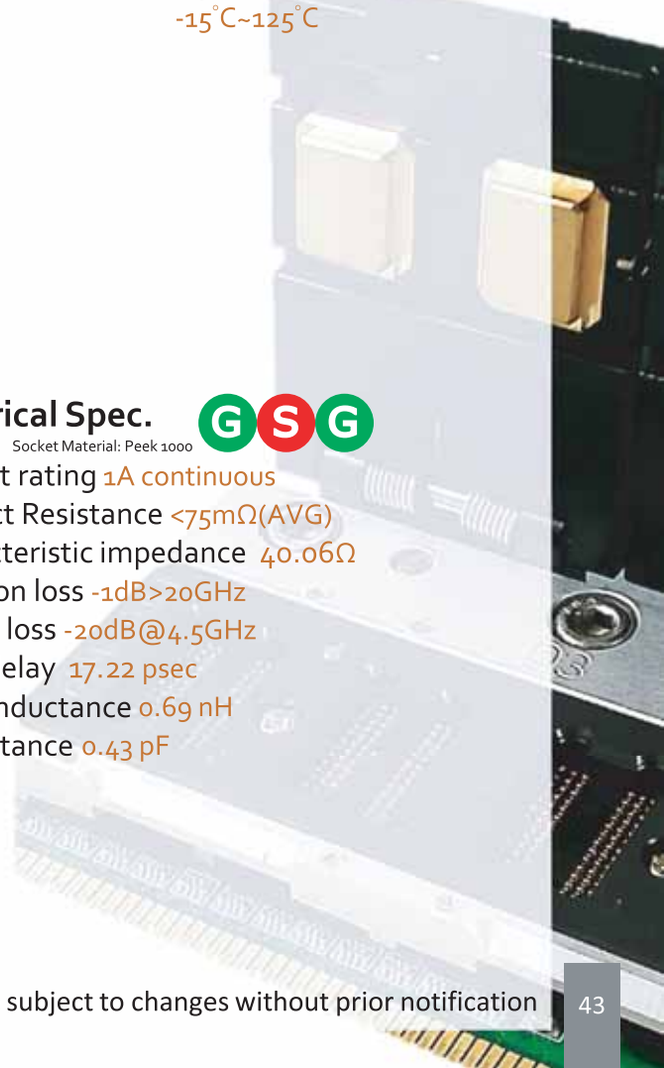
Pitch: 0.8mm Socket Material: Peek 1000

Current rating 1A continuous
Contact Resistance <75mΩ(AVG)
Characteristic impedance 41.2Ω
Insertion loss -1dB>20GHz
Return loss -20dB@ 2.56GHz
Time delay 32.2 psec
Loop inductance 1.33nH
Capacitance 0.78pF

Electrical Spec. G S G

Pitch: 0.5mm Socket Material: Peek 1000

Current rating 1A continuous
Contact Resistance <75mΩ(AVG)
Characteristic impedance 40.06Ω
Insertion loss -1dB>20GHz
Return loss -20dB@4.5GHz
Time delay 17.22 psec
Loop inductance 0.69 nH
Capacitance 0.43 pF



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